

Pch -30V -3.0A Middle Power MOSFET

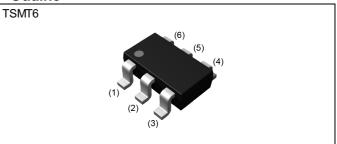
Datasheet

| V <sub>DSS</sub>           | -30V  |
|----------------------------|-------|
| R <sub>DS(on)</sub> (Max.) | 91mΩ  |
| I <sub>D</sub>             | ±3.0A |
| P <sub>D</sub>             | 1.25W |

### Features

- 1) Low on resistance.
- 2) Small Surface Mount Package (TSMT6).
- 3) Pb-free lead plating ; RoHS compliant

#### ●Outline



### ●Inner circuit

| <ul> <li>(1) Drain</li> <li>(2) Drain</li> <li>(3) Gate</li> <li>(4) Source</li> <li>(5) Drain</li> <li>(6) Drain</li> </ul> |             |
|--|-------------|
| *1 Body Diode  | (1) (2) (3) |

#### Packaging specifications

|      | Packing                   | Embossed<br>Tape |
|------|---------------------------|------------------|
|      | Reel size (mm)            | 180              |
| Туре | Tape width (mm)           | 8                |
|      | Basic ordering unit (pcs) | 3000             |
|      | Taping code               | TCR              |
|      | Marking                   | JS               |

### Application

Switching

### • Absolute maximum ratings ( $T_a = 25^{\circ}C$ )

| Parameter                      | Symbol                  | Value       | Unit |
|--------------------------------|-------------------------|-------------|------|
| Drain - Source voltage         | V <sub>DSS</sub>        | -30         | V    |
| Continuous drain current       | I <sub>D</sub>          | ±3.0        | А    |
| Pulsed drain current           | I <sub>D,pulse</sub> *2 | ±12         | А    |
| Gate - Source voltage          | V <sub>GSS</sub>        | ±20         | V    |
| Avalanche energy, single pulse | E <sub>AS</sub> *3      | 3.3         | mJ   |
| Avalanche current              | I <sub>AS</sub> *3      | -3.0        | А    |
| Power dissipation              | P <sub>D</sub> *4       | 1.25        | W    |
| Junction temperature           | Tj                      | 150         | °C   |
| Range of storage temperature   | T <sub>stg</sub>        | -55 to +150 | C°   |

### •Thermal resistance

| Parameter                              | Symbol          | Values |      |      | Linit |
|--|-----------------|--------|------|------|-------|
|  |                 | Min.   | Тур. | Max. | Unit  |
| Thermal resistance, junction - ambient | $R_{thJA}^{*4}$ | -      | 100  | -    | °C/W  |

### •Electrical characteristics (T<sub>a</sub> = 25°C)

| Deremeter                                      | Sumbol   | Conditions                                      | Values |      |      | Linit |
|--|--|---|--------|------|------|-------|
| Parameter                                      | Symbol   | Conditions                                      | Min.   | Тур. | Max. | Unit  |
| Drain - Source breakdown<br>voltage            | V <sub>(BR)DSS</sub>   | $V_{(BR)DSS}$ $V_{GS} = 0V, I_D = -1mA$         |        | -    | -    | V     |
| Breakdown voltage<br>temperature coefficient   | $\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}} I_{D} = 1 \text{mA}$ referenced to 25°C |   | -      | -22  | -    | mV/°C |
| Zero gate voltage<br>drain current             | $V_{DS} = -30V, V_{GS} = 0V$   |   | -      | -    | -1   | μA    |
| Gate - Source leakage current                  | I <sub>GSS</sub>   | $I_{GSS}$ $V_{GS}$ = ±20V, $V_{DS}$ = 0V        |        | -    | ±100 | nA    |
| Gate threshold voltage                         | V <sub>GS(th)</sub>  | $V_{DS} = V_{GS}$ , $I_D = -1mA$                | -1.0   | -    | -2.5 | V     |
| Gate threshold voltage temperature coefficient | $\frac{\Delta V_{GS(th)}}{\Delta T_j}$   |   |        | 2.9  | -    | mV/°C |
| Static drain - source                          | D *5   | V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.0A  | -      | 70   | 91   | m0    |
| on - state resistance                          | ${\sf R}_{\sf DS(on)}^{*5}$  | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.0A | -      | 104  | 135  | mΩ    |
| Transconductance                               | ${\sf g_{fs}}^{*5}$  | V <sub>DS</sub> = -5V, I <sub>D</sub> = -3.0A   | 2.4    | -    | -    | S     |

\*1 Limited only by maximum temperature allowed.

\*2 Pw  $\leq$  10µs, Duty cycle  $\leq$  1%

\*3 L  $\simeq$  0.5mH, V\_{DD} = -15V, R\_G = 25 $\Omega$ , STARTING T\_{ch} = 25°C Fig.3-1,3-2

\*4 Mounted on a ceramic boad (30×30×0.8mm)

\*5 Pulsed



# •Electrical characteristics (T<sub>a</sub> = 25°C)

| Deremeter                    | Symbol                | Conditions                          | Values |      |      | Unit |
|------------------------------|-----------------------|-------------------------------------|--------|------|------|------|
| Parameter                    | Symbol                | Conditions                          | Min.   | Тур. | Max. | Unit |
| Input capacitance            | C <sub>iss</sub>      | V <sub>GS</sub> = 0V                | -      | 240  | -    |      |
| Output capacitance           | C <sub>oss</sub>      | V <sub>DS</sub> = -15V              | -      | 45   | -    | pF   |
| Reverse transfer capacitance | C <sub>rss</sub>      | f = 1MHz                            | -      | 35   | -    |      |
| Turn - on delay time         | t <sub>d(on)</sub> *5 | $V_{DD} \simeq -15V, V_{GS} = -10V$ | -      | 6.5  | -    |      |
| Rise time                    | t <sub>r</sub> *5     | I <sub>D</sub> = -1.5A              | -      | 8.5  | -    |      |
| Turn - off delay time        | $t_{d(off)}$ *5       | R <sub>L</sub> = 10Ω                | -      | 22   | -    | ns   |
| Fall time                    | t <sub>f</sub> *5     | R <sub>G</sub> = 10Ω                | -      | 5.5  | -    |      |

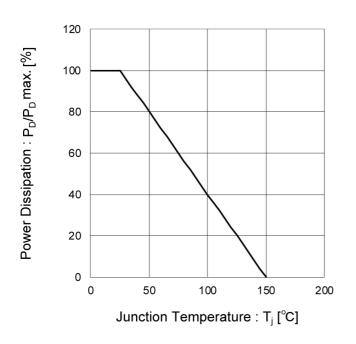
## • Gate charge characteristics ( $T_a = 25^{\circ}C$ )

| Parameter                          | Symbol            | Conditi                | Conditions              |      | Values |      |      |
|------------------------------------|-------------------|------------------------|-------------------------|------|--------|------|------|
|                                    | Symbol Conditions |                        | UIIS                    | Min. | Тур.   | Max. | Unit |
| Total acts allowed O <sup>*5</sup> |                   | V <sub>GS</sub> = -10  | V <sub>GS</sub> = -10V  | -    | 5.4    | -    |      |
| Total gate charge                  | $Q_g^{*5}$        | $V_{DD} \simeq -15V$   | 5V                      | -    | 2.7    | -    |      |
| Gate - Source charge               | $Q_{gs}^{*5}$     | I <sub>D</sub> = -3.0A | V <sub>GS</sub> = -4.5V | -    | 0.8    | -    | nC   |
| Gate - Drain charge                | $Q_{gd}^{*5}$     |                        |                         | -    | 1.0    | -    |      |

### •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

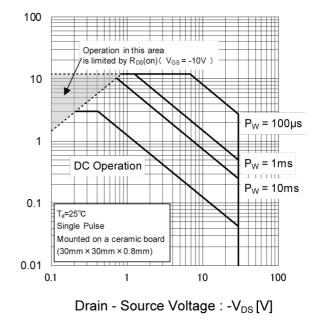
| Parameter                             | Symbol             | Conditions                                   | Values |      |      | Unit |  |
|---------------------------------------|--------------------|--|--------|------|------|------|--|
| Parameter Syr                         |                    | Symbol Conditions                            |        | Тур. | Max. | Unit |  |
| Body diode continuous forward current | ۱ <sub>S</sub> *1  | T - 25°0                                     | -      | -    | -1.0 | •    |  |
| Body diode<br>pulse current           | ا <sub>SP</sub> *2 | T <sub>a</sub> = 25℃                         | -      | -    | -12  | A    |  |
| Forward voltage                       | V <sub>SD</sub> *5 | V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.0A | -      | -    | -1.2 | V    |  |





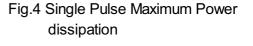
#### Fig.1 Power Dissipation Derating Curve

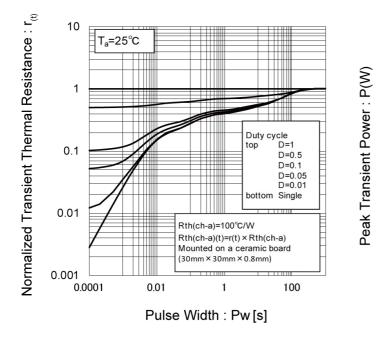
Fig.2 Maximum Safe Operating Area

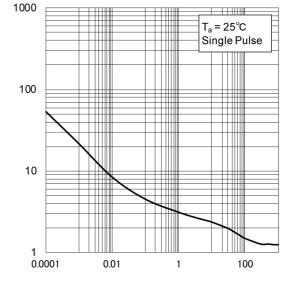


Drain Current : -I<sub>D</sub> [A]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

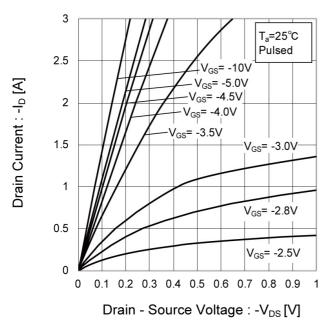




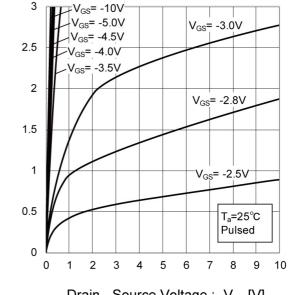


 $Pulse \ Width: Pw [s]$ 





#### Fig.5 Typical Output Characteristics(I)



#### Fig.6 Typical Output Characteristics(II)

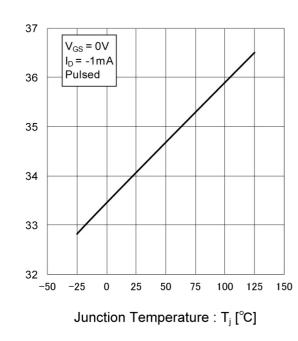
3

Drain Current : -I<sub>D</sub> [A]

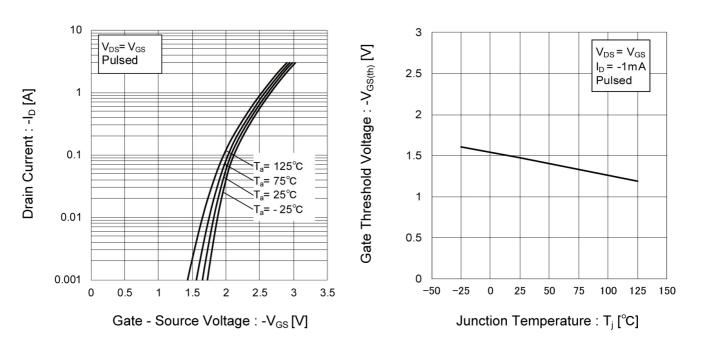
Drain - Source Voltage : -V<sub>DS</sub> [V]

### Fig.7 Breakdown Voltage vs. Junction Temperature

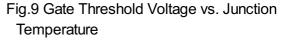
Drain-Source Breakdown Voltage : -V<sub>(BR)DSS</sub> [V]



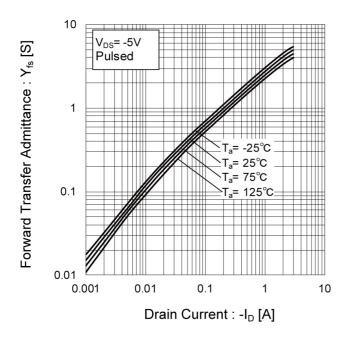




### Fig.8 Typical Transfer Characteristics



### Fig.10 Transconductance vs. Drain Current





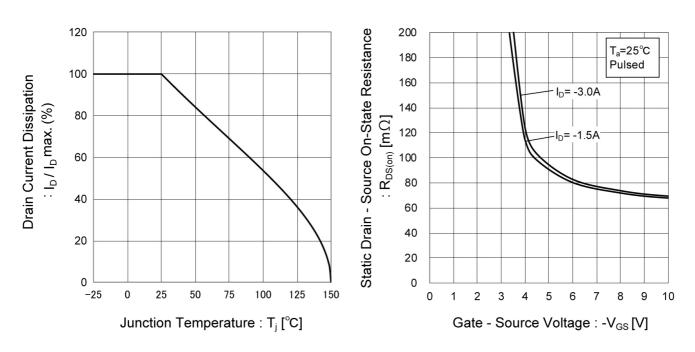


Fig.11 Drain Current Derating Curve

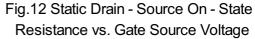
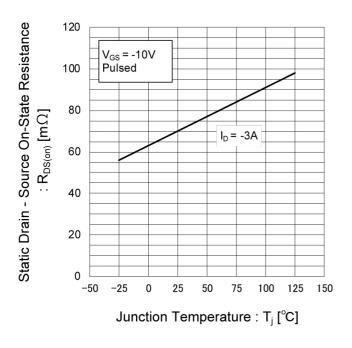


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature





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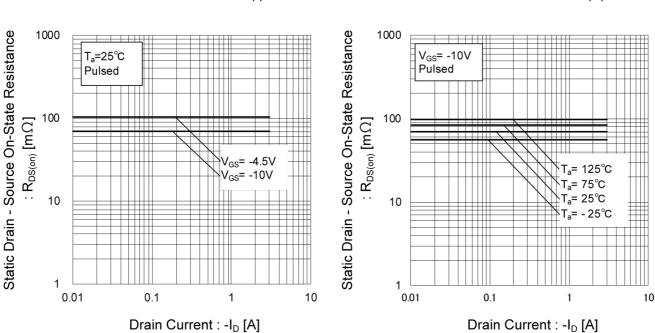
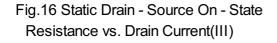
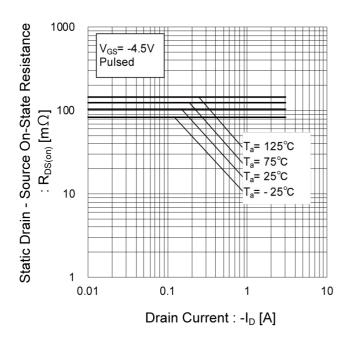
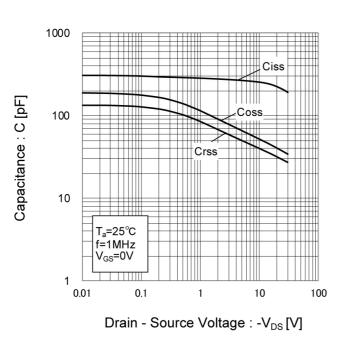


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I) Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)









## Fig.17 Typical Capacitance vs. Drain -Source Voltage

Fig.18 Switching Characteristics

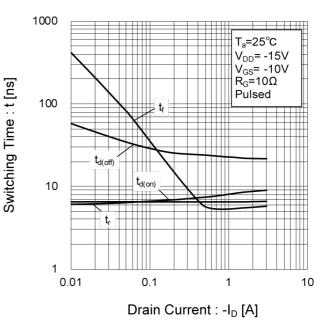


Fig.19 Dynamic Input Characteristics

Gate - Source Voltage : -V<sub>GS</sub> [V]

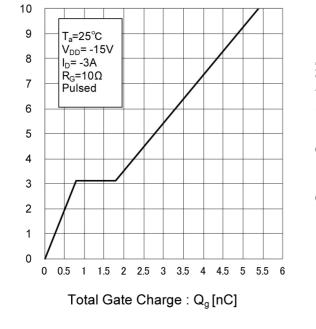
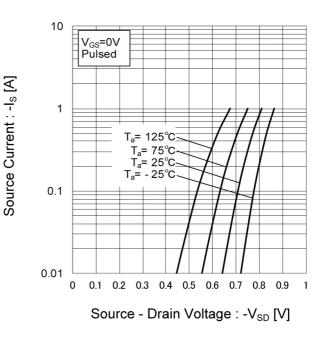


Fig.20 Source Current vs. Source Drain Voltage





#### Measurement circuits



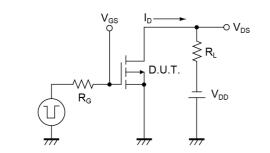


Fig.2-1 Gate Charge Measurement Circuit

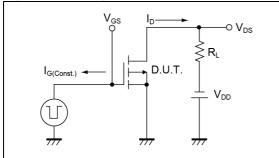
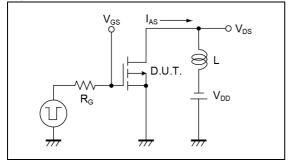


Fig.3-1 Avalanche Measurement Circuit



#### Fig.1-2 Switching Waveforms

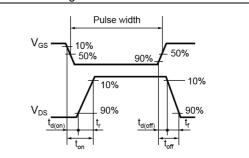


Fig.2-2 Gate Charge Waveform

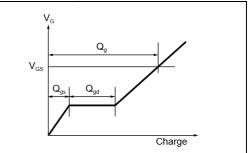
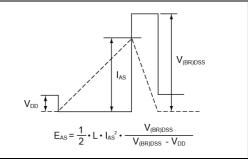
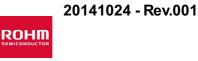


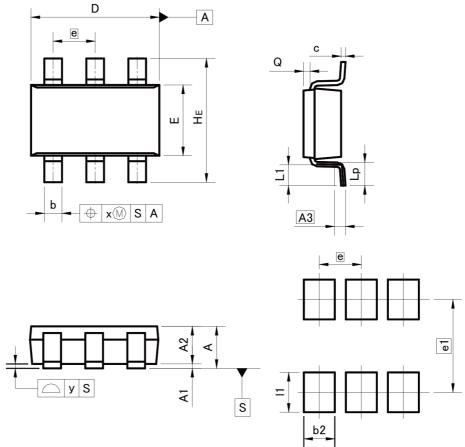
Fig.3-2 Avalanche Waveform





#### Dimensions

TSMT6



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

| DIM | MILIMETERS |       | INC   | HES   |  |
|-----|------------|-------|-------|-------|--|
| DIM | MIN        | MAX   | MIN   | MAX   |  |
| А   | -          | 1.00  | -     | 0.039 |  |
| A1  | 0.00       | 0.10  | 0.000 | 0.004 |  |
| A2  | 0.75       | 0.95  | 0.030 | 0.037 |  |
| A3  | 0.1        | 25    | 0.0   | )10   |  |
| b   | 0.35       | 0.50  | 0.014 | 0.020 |  |
| С   | 0.10       | 0.26  | 0.004 | 0.010 |  |
| D   | 2.80       | 3.00  | 0.110 | 0.118 |  |
| E   | 1.50       | 1.80  | 0.059 | 0.071 |  |
| е   | 0.95       |       | 0.037 |       |  |
| HE  | 2.60       | 3.00  | 0.102 | 0.118 |  |
| L1  | 0.30       | 0.60  | 0.012 | 0.024 |  |
| Lp  | 0.40       | 0.70  | 0.016 | 0.028 |  |
| Q   | 0.05       | 0.25  | 0.002 | 0.010 |  |
| х   | -          | 0.20  | -     | 0.008 |  |
| У   | -          | 0.10  | -     | 0.004 |  |
|     |            |       |       |       |  |
| DIM | MILIM      | ETERS | INC   | HES   |  |
|     | MIN        | MAX   | MIN   | MAX   |  |
| b2  |            | 0.70  | -     | 0.028 |  |
| e1  | 2.         | 10    | 0.0   | 83    |  |
| 1   | _          | 0.90  | _     | 0.035 |  |

Dimension in mm/inches





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|---|
|---|

| JÁPAN  | USA     | EU         | CHINA   |
|--------|---------|------------|---------|
| CLASSⅢ | CLASSⅢ  | CLASS II b | CLASSII |
| CLASSⅣ | CLASSII | CLASSⅢ     | CLASSI  |

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  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
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  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
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Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию.

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России, а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научноисследовательскими институтами России.

С нами вы становитесь еще успешнее!

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